

Zbigniew R Zytzkiewicz

List of Publications by Year in descending order

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146
papers

1,325
citations

393982

19
h-index

500791

28
g-index

147
all docs

147
docs citations

147
times ranked

1160
citing authors

#	ARTICLE	IF	CITATIONS
1	Influence of substrate nitridation temperature on epitaxial alignment of GaN nanowires to Si(111) substrate. <i>Nanotechnology</i> , 2013, 24, 035703.	1.3	74
2	Laterally overgrown structures as substrates for lattice mismatched epitaxy. <i>Thin Solid Films</i> , 2002, 412, 64-75.	0.8	66
3	Evidence for substitutional-interstitial defect motion leading to DX behavior by donors in $\text{Al}_x\text{Ga}_{1-x}\text{As}$. <i>Physical Review Letters</i> , 1992, 68, 2508-2511.	2.9	62
4	Epitaxial Lateral Overgrowth of GaAs: Principle and Growth Mechanism. <i>Crystal Research and Technology</i> , 1999, 34, 573-582.	0.6	39
5	Structure of the DX state formed by donors in $(\text{Al,Ga})\text{As}$ and $\text{Ga}(\text{As,P})$. <i>Journal of Applied Physics</i> , 1995, 78, 2468-2477.	1.1	30
6	Growth by molecular beam epitaxy and properties of inclined GaN nanowires on Si(001) substrate. <i>Nanotechnology</i> , 2014, 25, 135610.	1.3	28
7	Enhanced catalyst-free nucleation of GaN nanowires on amorphous Al_2O_3 by plasma-assisted molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2014, 115, 043517.	1.1	27
8	Contactless electroreflectance studies of the Fermi level position at the air/GaN interface: Bistable nature of the Ga-polar surface. <i>Applied Surface Science</i> , 2017, 396, 1657-1666.	3.1	27
9	Plasma-assisted MBE growth of GaN on Si(111) substrates. <i>Crystal Research and Technology</i> , 2012, 47, 307-312.	0.6	26
10	Analysis of Incubation Times for the Self-Induced Formation of GaN Nanowires: Influence of the Substrate on the Nucleation Mechanism. <i>Crystal Growth and Design</i> , 2016, 16, 7205-7211.	1.4	26
11	Dynamics of stacking faults luminescence in GaN/Si nanowires. <i>Journal of Luminescence</i> , 2014, 155, 293-297.	1.5	24
12	Optimization of nitrogen plasma source parameters by measurements of emitted light intensity for growth of GaN by molecular beam epitaxy. <i>Thin Solid Films</i> , 2013, 534, 107-110.	0.8	23
13	Self-assembled growth of GaN nanowires on amorphous Al_xO_y : from nucleation to the formation of dense nanowire ensembles. <i>Nanotechnology</i> , 2016, 27, 325601.	1.3	23
14	Joule effect as a barrier for unrestricted growth of bulk crystals by liquid phase electroepitaxy. <i>Journal of Crystal Growth</i> , 1997, 172, 259-268.	0.7	21
15	Microscopic bending of GaAs layers grown by epitaxial lateral overgrowth. <i>Journal of Applied Physics</i> , 1998, 84, 6937-6939.	1.1	21
16	Arrangement of GaN nanowires grown by plasma-assisted molecular beam epitaxy on silicon substrates with amorphous Al_2O_3 buffers. <i>Journal of Crystal Growth</i> , 2014, 401, 657-660.	0.7	21
17	Kinetics of self-induced nucleation and optical properties of GaN nanowires grown by plasma-assisted molecular beam epitaxy on amorphous Al_xO_y . <i>Journal of Applied Physics</i> , 2015, 118, .	1.1	21
18	High-resolution X-ray diffraction analysis of strain distribution in GaN nanowires on Si(111) substrate. <i>Nanoscale Research Letters</i> , 2015, 10, 51.	3.1	21

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19	Thermal strain in GaAs layers grown by epitaxial lateral overgrowth on Si substrates. Applied Physics Letters, 1999, 75, 2749-2751.	1.5	20
20	Influence of convection on the composition profiles of thick GaAlAs layers grown by liquid phase electroepitaxy. Journal of Crystal Growth, 1993, 131, 426-430.	0.7	19
21	Epitaxial lateral overgrowth of GaAs: effect of doping on LPE growth behaviour. Semiconductor Science and Technology, 1999, 14, 465-469.	1.0	19
22	Piezoscopic deep-level transient spectroscopy studies of the silicon divacancy. Physical Review B, 2002, 65, .	1.1	19
23	Compositional control of thick Ga _{1-x} Al _x As layers (x=0.72) grown by liquid phase electroepitaxy. Journal of Crystal Growth, 1992, 121, 457-462.	0.7	18
24	Strain in GaAs layers grown by liquid phase epitaxial lateral overgrowth. Journal of Applied Physics, 1999, 86, 1965-1969.	1.1	18
25	Hole capture at the DX(Si) and DX(Te) defects in Al _x Ga _{1-x} As. Journal of Applied Physics, 1992, 72, 3198-3200.	1.1	17
26	Control of adhesion to the mask of epitaxial laterally overgrown GaAs layers. Journal of Applied Physics, 2001, 90, 6140-6144.	1.1	17
27	Synchrotron x-ray topographic and high-resolution diffraction analysis of mask-induced strain in epitaxial laterally overgrown GaAs layers. Journal of Applied Physics, 1999, 86, 4298-4303.	1.1	16
28	Determination of crystal misorientation in epitaxial lateral overgrowth of GaN. Journal of Crystal Growth, 2002, 243, 94-102.	0.7	16
29	Anisotropic Misfit Strain Relaxation in Thin Epitaxial Layers. Physica Status Solidi A, 1999, 171, 289-294.	1.7	14
30	A model for epitaxial lateral overgrowth of GaAs by liquid-phase electroepitaxy. Journal of Crystal Growth, 2004, 265, 341-350.	0.7	14
31	Interaction of iron with the local environment in SiGe alloys investigated with Laplace transform deep level spectroscopy. Physical Review B, 2006, 74, .	1.1	14
32	Imaging of strain in laterally overgrown GaAs layers by spatially resolved x-ray diffraction. Applied Physics Letters, 2007, 90, 241904.	1.5	14
33	Chemical bonding of nitrogen formed by nitridation of crystalline and amorphous aluminum oxide studied by X-ray photoelectron spectroscopy. RSC Advances, 2020, 10, 27932-27939.	1.7	14
34	Coupled plasmon-LO-phonon modes at high-magnetic fields. Physical Review B, 2006, 74, .	1.1	13
35	Optical properties of pure and Ce ³⁺ doped gadolinium gallium garnet crystals and epitaxial layers. Journal of Luminescence, 2015, 164, 31-37.	1.5	13
36	Liquid phase electroepitaxial growth of thick and compositionally uniform AlGaAs layers on GaAs substrates. Journal of Crystal Growth, 1995, 146, 283-286.	0.7	12

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37	Tilt and dislocations in epitaxial laterally overgrown GaAs layers. <i>Journal of Applied Physics</i> , 2007, 101, 013508.	1.1	12
38	Deep levels in GaN studied by deep level transient spectroscopy and Laplace transform deep-level spectroscopy. <i>Materials Science-Poland</i> , 2013, 31, 572-576.	0.4	12
39	Modelling of X-ray diffraction curves for GaN nanowires on Si(1 1 1). <i>Journal of Crystal Growth</i> , 2014, 401, 347-350.	0.7	12
40	Electroepitaxy from a limited solution volume: Growth kinetics calculations. <i>Journal of Crystal Growth</i> , 1983, 61, 665-674.	0.7	11
41	Synchrotron x-ray topography analysis of GaAs layers grown on GaAs substrates by liquid phase epitaxial lateral overgrowth. <i>Journal Physics D: Applied Physics</i> , 1999, 32, A114-A118.	1.3	11
42	Structure modifications in silicon irradiated by ultra-short pulses of XUV free electron laser. <i>Journal of Alloys and Compounds</i> , 2004, 382, 264-270.	2.8	11
43	Electrical characterization of ensemble of GaN nanowires grown by the molecular beam epitaxy technique. <i>Applied Physics Letters</i> , 2013, 103, .	1.5	11
44	Determination of Fermi Level Position at the Graphene/GaN Interface Using Electromodulation Spectroscopy. <i>Advanced Materials Interfaces</i> , 2020, 7, 2001220.	1.9	11
45	Influence of Substrate on Crystallographic Quality of AlGaIn/GaN HEMT Structures Grown by Plasma-Assisted MBE. <i>Acta Physica Polonica A</i> , 2012, 121, 899-902.	0.2	11
46	Recent progress in lateral overgrowth of semiconductor structures from the liquid phase. <i>Crystal Research and Technology</i> , 2005, 40, 321-328.	0.6	10
47	Crystal Defects and Strain of Epitaxial InP Layers Laterally Overgrown on Si. <i>Crystal Growth and Design</i> , 2006, 6, 1096-1100.	1.4	10
48	Engineering of electric field distribution in GaN(cap)/AlGaIn/GaN heterostructures: theoretical and experimental studies. <i>Journal Physics D: Applied Physics</i> , 2016, 49, 345106.	1.3	10
49	Arrangement of GaN nanowires on Si(001) substrates studied by X-ray diffraction: Importance of silicon nitride interlayer. <i>Applied Surface Science</i> , 2017, 425, 1014-1019.	3.1	10
50	Influence of high hydrostatic pressure and high temperature treatment on defect structure of AlGaAs layers. <i>Journal of Alloys and Compounds</i> , 1999, 286, 279-283.	2.8	9
51	Epitaxial lateral overgrowth of GaSb layers by liquid phase epitaxy. <i>Journal of Crystal Growth</i> , 2003, 253, 102-106.	0.7	9
52	X-ray diffraction micro-imaging of strain in laterally overgrown GaAs layers. Part I: analysis of a single GaAs stripe. <i>Applied Physics A: Materials Science and Processing</i> , 2008, 91, 601-607.	1.1	9
53	Enhanced Raman scattering and weak localization in graphene deposited on GaN nanowires. <i>Physical Review B</i> , 2015, 92, .	1.1	9
54	An influence of the local strain on cathodoluminescence of GaN/Al _x Ga _{1-x} N nanowire structures. <i>Journal of Applied Physics</i> , 2016, 120, .	1.1	9

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55	Experimental and theoretical analysis of influence of barrier composition on optical properties of GaN/AlGa _x N multi-quantum wells: Temperature- and pressure-dependent photoluminescence studies. Journal of Alloys and Compounds, 2018, 769, 1064-1071.	2.8	9
56	Comprehensive analysis of the self-assembled formation of GaN nanowires on amorphous Al _x O _y : <i>in situ</i> quadrupole mass spectrometry studies. Nanotechnology, 2019, 30, 154002.	1.3	9
57	Defect-related photoluminescence and photoluminescence excitation as a method to study the excitonic bandgap of AlN epitaxial layers: Experimental and <i>ab initio</i> analysis. Applied Physics Letters, 2020, 117, .	1.5	9
58	Lattice constants and thermal expansion of Al _x Ga _{1-x} As:Te. Journal of Applied Physics, 1995, 78, 6994-6998.	1.1	8
59	Selective area formation of GaN nanowires on GaN substrates by the use of amorphous Al _x O _y nucleation layer. Nanotechnology, 2020, 31, 184001.	1.3	8
60	Surface-enhanced Raman scattering of graphene caused by self-induced nanogating by GaN nanowire array. Carbon, 2018, 128, 70-77.	5.4	8
61	X ₁ -X ₃ conduction-band splitting of Al _x Ga _{1-x} As observed in far-infrared photoinduced absorption related to the DX defect. Physical Review B, 1993, 47, 12558-12562.	1.1	7
62	Magnetic-resonance studies of tellurium-doped Al _x Ga _{1-x} As. Physical Review B, 1994, 50, 2645-2648.	1.1	7
63	Mask-Induced Strain in GaAs Layers Grown by Liquid Phase Epitaxial Lateral Overgrowth. Materials Research Society Symposia Proceedings, 1999, 570, 273.	0.1	7
64	Deep traps in n-type GaN epilayers grown by plasma assisted molecular beam epitaxy. Journal of Applied Physics, 2014, 115, 023102.	1.1	7
65	Surface-enhanced Raman scattering in graphene deposited on Al _x Ga _{1-x} N/GaN axial heterostructure nanowires. Applied Surface Science, 2019, 475, 559-564.	3.1	7
66	Compositionally Graded AlGa _x N Nanostructures: Strain Distribution and X-ray Diffraction Reciprocal Space Mapping. Crystal Growth and Design, 2020, 20, 1543-1551.	1.4	7
67	Hybrid P3HT: PCBM/GaN nanowire/Si cascade heterojunction for photovoltaic application. Journal of Nanoparticle Research, 2020, 22, 1.	0.8	7
68	Photoluminescence Dynamics of GaN/Si Nanowires. Acta Physica Polonica A, 2012, 122, 1001-1003.	0.2	7
69	Effect of stress on interface transformation in thin semiconducting layers. Thin Solid Films, 2000, 380, 117-119.	0.8	6
70	X-ray diffraction studies of epitaxial laterally overgrown (ELOG) GaN layers on sapphire substrates. Journal of Crystal Growth, 2002, 245, 37-49.	0.7	6
71	Application of tungsten films for substrate masking in liquid phase epitaxial lateral overgrowth of GaAs. Crystal Research and Technology, 2003, 38, 297-301.	0.6	6
72	Properties of ZrN films as substrate masks in liquid phase epitaxial lateral overgrowth of compound semiconductors. Crystal Research and Technology, 2005, 40, 492-497.	0.6	6

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73	Stable and metastable configurations of iron atoms in SiGe alloys. <i>Journal of Physics Condensed Matter</i> , 2005, 17, S2267-S2272.	0.7	6
74	Structural and optical characterization of GaN nanowires. <i>Journal of Applied Physics</i> , 2013, 113, .	1.1	6
75	Application of ZnO single crystals for light-induced water splitting under UV irradiation. <i>Materials Chemistry and Physics</i> , 2014, 143, 1253-1257.	2.0	6
76	Surface Diffusion of Gallium as the Origin of Inhomogeneity in Selective Area Growth of GaN Nanowires on Al _x O _y Nucleation Stripes. <i>Crystal Growth and Design</i> , 2020, 20, 4770-4778.	1.4	6
77	Epitaxial Lateral Overgrowth of Semiconductors. , 2010, , 999-1039.		6
78	The Impact of Bulk Defects, Surface States, and Excitons on Yellow and Ultraviolet Photoluminescence in GaN. <i>Acta Physica Polonica A</i> , 2011, 120, A-73-A-75.	0.2	6
79	Computational analysis of lateral overgrowth of GaAs by liquid-phase epitaxy. <i>Journal of Crystal Growth</i> , 2005, 275, e953-e957.	0.7	5
80	Epitaxial lateral overgrowth of semiconductor structures by liquid phase epitaxy. <i>International Journal of Materials and Product Technology</i> , 2005, 22, 50.	0.1	5
81	Influence of AlN layer on electric field distribution in GaN/AlGaIn/GaN transistor heterostructures. <i>Journal of Applied Physics</i> , 2013, 114, .	1.1	5
82	High-temperature ultraviolet detection based on surface photovoltage effect in SiN passivated n-GaN films. <i>Applied Physics Letters</i> , 2016, 109, .	1.5	5
83	Substrate Defects Filtration During Epitaxial Lateral Overgrowth of GaAs. <i>Acta Physica Polonica A</i> , 1997, 92, 1079-1082.	0.2	5
84	Lattice matching in Ga _x In _{1-x} As _y P _{1-y} -GaAs and Ga _x In _{1-x} As _y P _{1-y} -InP structures. <i>Physica Status Solidi A</i> , 1979, 53, K165-K168.	1.7	4
85	X-ray diffraction micro-imaging of strain in laterally overgrown GaAs layers. Part II: analysis of multi-stripe and fully overgrown layers. <i>Applied Physics A: Materials Science and Processing</i> , 2008, 91, 609-614.	1.1	4
86	Electrical characterisation of GaN and AlGaIn layers grown by plasma-assisted MBE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012, 9, 1043-1047.	0.8	4
87	Ga _x In _{1-x} As _y P _{1-y} /GaAs structure: Liquid phase epitaxial growth and analysis of lattice constants matching conditions. <i>Physica Status Solidi A</i> , 1980, 57, 489-497.	1.7	3
88	On the nature of the edge growth in liquid phase epitaxy of GaAs. <i>Journal of Crystal Growth</i> , 1989, 94, 919-922.	0.7	3
89	Pressure-induced defect structure changes in thin AlGaAs layers. <i>Journal of Alloys and Compounds</i> , 2004, 362, 254-260.	2.8	3
90	Spatially resolved x-ray diffraction study of GaSb layers grown laterally on SiO ₂ -masked GaAs substrates. <i>Journal of Applied Physics</i> , 2009, 106, 043521.	1.1	3

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91	Numerical analysis of growth kinetics of bulk III-V crystals grown by liquid phase electroepitaxy. Crystal Research and Technology, 2010, 45, 1290-1294.	0.6	3
92	Time dependent simulations of the growth of III-V crystals by the liquid phase electroepitaxy. Journal of Crystal Growth, 2011, 318, 351-355.	0.7	3
93	Reflectance and fast polarization dynamics of a GaN/Si nanowire ensemble. Journal of Physics Condensed Matter, 2018, 30, 315301.	0.7	3
94	Properties of graphene deposited on GaN nanowires: influence of nanowire roughness, self-induced nanogating and defects. Beilstein Journal of Nanotechnology, 2021, 12, 566-577.	1.5	3
95	Spatially Resolved X-ray Diffraction Technique for Crystallographic Quality Inspection of Semiconductor Microstructures. Acta Physica Polonica A, 2008, 114, 1101-1107.	0.2	3
96	Influence of Growth Polarity Switching on the Optical and Electrical Properties of GaN/AlGaIn Nanowire LEDs. Electronics (Switzerland), 2021, 10, 45.	1.8	3
97	Diffusion Limited LPE Growth of GaIn _x P on (100) GaAs. Physica Status Solidi A, 1991, 128, 123-127.	1.7	2
98	On the applicability of InGaP:Si and AlGaAs:Sn piezoresistive pressure sensors in the 2.5 GPa range. Sensors and Actuators A: Physical, 1999, 78, 130-137.	2.0	2
99	Epitaxial Lateral Overgrowth of Gallium Arsenide Studied by Synchrotron Topography. Materials Research Society Symposia Proceedings, 1999, 570, 181.	0.1	2
100	Measurements of strain in AlGaIn/GaN HEMT structures grown by plasma assisted molecular beam epitaxy. Journal of Crystal Growth, 2014, 401, 355-358.	0.7	2
101	Structural, electrical, and optical characterization of coalescent p-n GaN nanowires grown by molecular beam epitaxy. Journal of Applied Physics, 2015, 118, 224307.	1.1	2
102	GaN Nanowire Array for Charge Transfer in Hybrid GaN/P3HT:PC71BM Photovoltaic Heterostructure Fabricated on Silicon. Materials, 2020, 13, 4755.	1.3	2
103	Optical and Electrical Properties of Bulk GaSb and AlGaSb. Acta Physica Polonica A, 1995, 88, 763-766.	0.2	2
104	Effect of Doping on Ga _{1-x} Al _x As Structural Properties. Acta Physica Polonica A, 1997, 91, 911-917.	0.2	2
105	Photoinduced Defects Creation on Sulfur Passivated Surface of GaAs. Acta Physica Polonica A, 1997, 92, 1083-1086.	0.2	2
106	Epitaxial Lateral Overgrowth - a Tool for Dislocation Blockade in Multilayer Systems. Acta Physica Polonica A, 1998, 94, 219-227.	0.2	2
107	Determination of Ga _{1-x} Al _x As epitaxial layer composition by X-ray intensity measurements of quasi-forbidden reflections. Journal of Crystal Growth, 1993, 126, 168-173.	0.7	1
108	Evidence for Alloy Splitting of the Te DX State in Al _x Ga _{1-x} As. Materials Science Forum, 1994, 143-147, 1123-1128.	0.3	1

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109	Rietveld Refinement for Selected Pseudobinary Semiconductors. Materials Science Forum, 1996, 228-231, 689-694.	0.3	1
110	Electrical Properties of InGaP:Si and AlGaAs:Sn Epitaxial Layers. Physica Status Solidi (B): Basic Research, 1999, 211, 565-570.	0.7	1
111	Microdefects and nonstoichiometry level in GaAs:Si/GaAs films grown by liquid-phase epitaxy method. Journal of Alloys and Compounds, 2001, 328, 218-221.	2.8	1
112	Strain in epitaxial laterally overgrown (ELO) structures. , 2001, , .		1
113	The application of Makyoh topography for the study of GaAs layers grown by epitaxial lateral overgrowth. Journal of Crystal Growth, 2001, 222, 741-746.	0.7	1
114	Spatially resolved X-ray diffraction as a tool for strain analysis in laterally modulated epitaxial structures. Crystal Research and Technology, 2009, 44, 1089-1094.	0.6	1
115	Unlimited Growth of III-V Bulk Crystals by Liquid-Phase Electroepitaxy. Crystal Growth and Design, 2011, 11, 4684-4689.	1.4	1
116	Structural and Chemical Characterization of Al(Ga)N/GaN Quantum Well Structures Grown by Plasma Assisted Molecular Beam Epitaxy. Solid State Phenomena, 2012, 186, 70-73.	0.3	1
117	Influence of Si Substrate Preparation Procedure on Polarity of Self-Assembled GaN Nanowires on Si(111): Kelvin Probe Force Microscopy Studies. Electronics (Switzerland), 2020, 9, 1904.	1.8	1
118	Rocking Curve Imaging Studies of Laterally Overgrown GaAs and GaSb Epitaxial Layers. Acta Physica Polonica A, 2009, 116, 976-978.	0.2	1
119	New DX-Related Photoinduced Absorption in AlGaAs:Te. Acta Physica Polonica A, 1991, 80, 397-400.	0.2	1
120	A Role of Intermediate Charge State in the DX Center Photoionisation in Al _x Ga _{1-x} As:Se. Acta Physica Polonica A, 1992, 82, 801-804.	0.2	1
121	Anisotropic Lattice Misfit Relaxation in AlGaAs Semi-Bulk Layers Grown on GaAs Substrates by Liquid Phase Electroepitaxy. Acta Physica Polonica A, 1997, 92, 1092-1096.	0.2	1
122	New Local Vibrational Modes Related to Silicon in Bulk AlGaAs. Acta Physica Polonica A, 1995, 88, 759-762.	0.2	1
123	Strain control in graphene on GaN nanowires: Towards pseudomagnetic field engineering. Carbon, 2022, 186, 128-140.	5.4	1
124	Observation of the intermediate energy state of the DX centre in Al _x Ga _{1-x} As:Te in non-stationary absorption experiments. Semiconductor Science and Technology, 1993, 8, 1973-1976.	1.0	0
125	Static and Dynamic Absorption Measurements of the DX Center in Al _x Ga _{1-x} As. Materials Science Forum, 1994, 143-147, 1093-1098.	0.3	0
126	The use of Ga ₂ Se ₃ and Ga ₂ S ₃ as donor doping sources for MBE-grown Al _x Ga _{1-x} Sb and Al _x Ga _{1-x} As. Semiconductor Science and Technology, 1995, 10, 509-514.	1.0	0

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127	Silicon-Related Local Vibrational Mode Absorption in Bulk AlGaAs. Materials Science Forum, 1995, 196-201, 1091-1096.	0.3	0
128	New donor doping sources for molecular beam epitaxy of AlGaSb and AlGaAs. Materials Science and Technology, 1996, 12, 193-196.	0.8	0
129	Pressure sensors based on AlGaAs doped with Te and Sn. High Pressure Research, 2000, 19, 359-365.	0.4	0
130	Control of growth uniformity of III-V bulk crystals grown by contactless liquid phase electroepitaxy. Journal of Crystal Growth, 2012, 355, 1-7.	0.7	0
131	Optical and Electrical Studies of Graphene Deposited on GaN Nanowires. Acta Physica Polonica A, 2014, 126, 1087-1089.	0.2	0
132	X-ray Reciprocal Space Mapping of Graded Al _x Ga _{1-x} N Films and Nanowires. Nanoscale Research Letters, 2016, 11, 81.	3.1	0
133	P2.4.18 MBE growth of GaN nanowires on Si(111) substrates for gas sensor applications. , 2012, , .		0
134	The Growth and Micro-Raman Characterization of GaN Nanowires. Sensor Letters, 2013, 11, 1555-1559.	0.4	0
135	AlGaAs to GaAs Energy Transfer Mechanisms in AlGaAs/GaAs Structures. Acta Physica Polonica A, 1992, 82, 713-716.	0.2	0
136	Electron Spin Resonance Studies of Te Doped AlGaAs Epilayers. Acta Physica Polonica A, 1992, 82, 817-820.	0.2	0
137	Formation of the DX State by Donors in Al _x Ga _{1-x} As - Experiment. Acta Physica Polonica A, 1992, 82, 905-907.	0.2	0
138	Alloy Splitting of the Te-DX States in Al _x Ga _{1-x} As. Acta Physica Polonica A, 1993, 84, 769-772.	0.2	0
139	Molecular Beam Epitaxy of Al _x Ga _{1-x} Sb and Al _x Ga _{1-x} As: New Donor Doping Sources. Acta Physica Polonica A, 1993, 84, 826-828.	0.2	0
140	Photo-ESR Study of the DX to Shallow Donor Conversion in Te Doped Al _x Ga _{1-x} As. Acta Physica Polonica A, 1993, 84, 757-760.	0.2	0
141	Electroepitaxial Growth of GaSb and AlGaSb Thick Epitaxial Layers. Acta Physica Polonica A, 1995, 88, 965-968.	0.2	0
142	Lattice Sites of Silicon Impurities in AlGaAs Grown by Liquid Phase Epitaxy. Acta Physica Polonica A, 1996, 90, 865-868.	0.2	0
143	High-Pressure Diffraction Study of Ga _{1-x} Al _x As. Acta Physica Polonica A, 1997, 91, 993-996.	0.2	0
144	Influence of Si Doping on Epitaxial Lateral Overgrowth of GaAs. , 1998, , 71-74.		0

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145	Investigating the secondary electron emission of nanomaterials induced by a high resolution proton beam. <i>Physica Status Solidi (B): Basic Research</i> , 0, , .	0.7	0
146	Alternative Route of Fracturing in GaN Films Formed by Nanowires Coalescence on Si Substrate. <i>Crystal Growth and Design</i> , 2022, 22, 3264-3270.	1.4	0